

**ELECTRICAL CHARACTERISTICS: OM400L60CMS (Tc= 25°C unless otherwise specified)**

Characteristic	Symbol	Min.	Typ.	Max	Unit
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OFF CHARACTERISTICS

Collector Emitter Breakdown Voltage, VCE=0V	VCES	600			V
Zero Gate Voltage Drain Current, VGE=0, VCE =600V	ICES		25		μA
Gate Emitter Leakage Current, VGE=+/-15V, VCE=0V	IGES			2	μA

ON CHARACTERISTICS

Gate Threshold Voltage, VCE=VGE, IC=6mA	VGE(TH)	4.5		6.5	V
Collector Emitter Saturation Voltage, VGE=15V, IC=400A	VCE(SAT)		2.4	2.7	V

DYNAMIC CHARACTERISTICS

Fwd. Transconductance	VCE=5V, IC=400A	gfs		42	S
Input Capacitance	VGE=0	Cies		20000	pF
Output Capacitance	VCE=25V	Coes		1080	pF
Rev. Transfer Capacitance	f=1.0MHz	Cres		1120	pF

SWITCHING INDUCTIVE LOAD CHARACTERISTICS

Turn-On Delay Time	VCC= 300V, IC=400A VGE=+15/-10V, RG=6.8Ω L=100μH, Tj=125°C	t(on)		800	1600	nS
Rise Time		tr		400	800	nS
Turn-on Losses		Eon		20		mJ
Turn-off Delay Time		td(off)		800	1200	nS
Fall Time		tf		350	800	nS
Turn-off Losses		Eoff		25		mJ

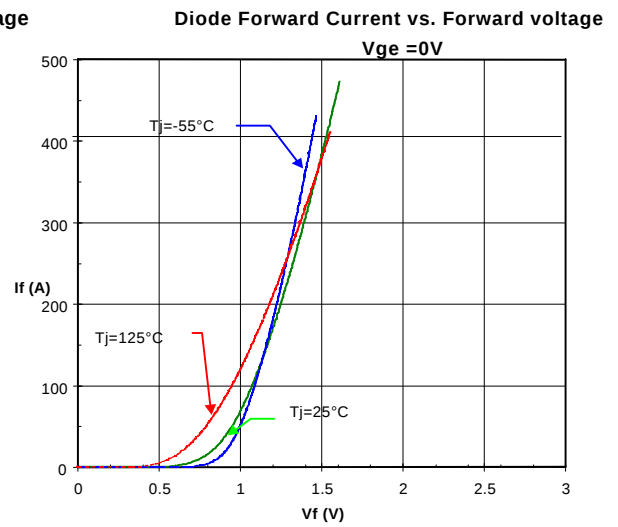
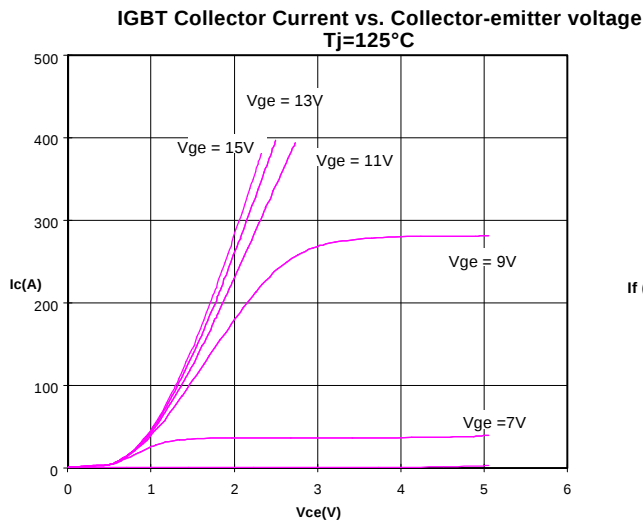
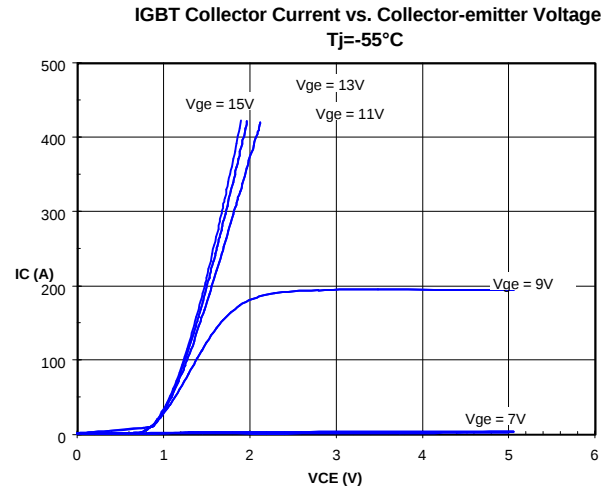
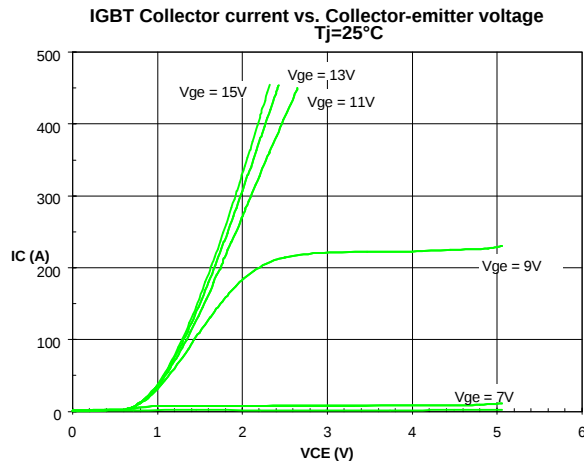
DIODE CHARACTERISTICS

Maximum Forward Voltage	IF=400A, Tj=25°C Tj=125°C	VF		1.5	2.0	V
Reverse Recovery Characteristics	VR=300V, Tj=25°C IF=400A, Tj=125°C dI/dt=-1500A/μS Tj=25°C Tj=125°C Tj=25°C Tj=125°C	Qrr		10		μC
				24		
		Irr		60		A
				90		
		trr		160		nS
				220		

THERMAL AND MECHANICAL CHARACTERISTICS

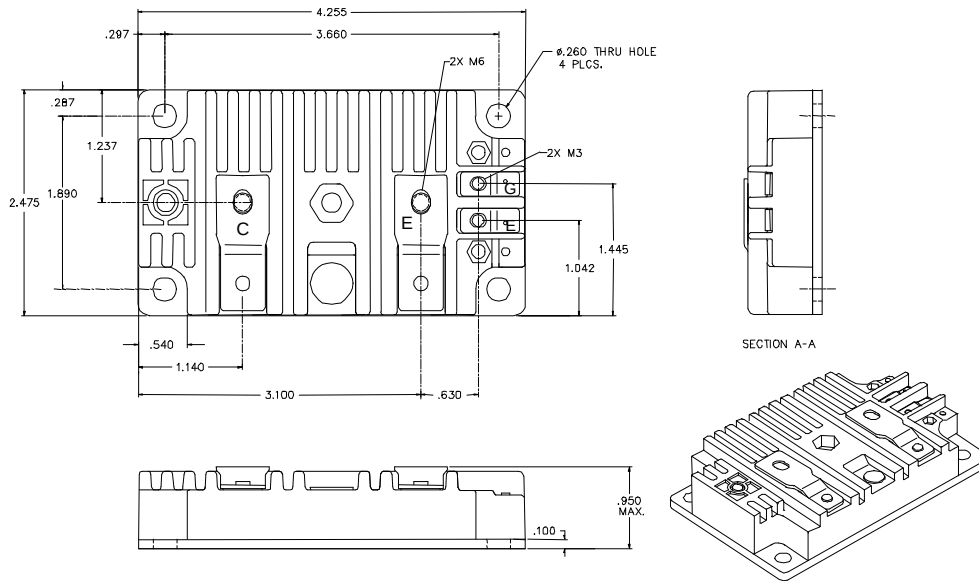
Thermal Resistance, Junction to Case (Per IGBT)	RthJC			0.085	°C/W
Thermal Resistance, Junction to Case (Per Diode)	RthJC			0.15	°C/W
Maximum Junction Temperature	TjMAX			150	°C
Isolation Voltage	ViSRMS			2500	V
Screw Torque	Mounting	-	15	20	in-lb
Screw Torque (M6)	Terminals	-	10	12	in-lb
Screw Torque (M3)	Terminals	-	6	8	in-lb
Module Weight	-			400	Grams

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MECHANICAL OUTLINE



EQUIVALENT CIRCUIT

